

IN THE ABSTRACT

*Please amend the abstract on page 30 as follows.*

A method of fabricating a semiconductor device including a first wiring pattern extending in a vertical direction and a second wiring pattern identical in geometry to the first wiring pattern and extending in a (horizontal) direction orthogonal to the vertical direction, including the steps of: employing linearly polarized illumination to perform exposure along a mask pattern including mask patterns (16, 17) used to form the first and second wiring patterns, respectively; and subsequently forming the first and second wiring patterns having a geometry along the mask patterns. The mask patterns to form the first and second wiring patterns are formed to be different in geometry.